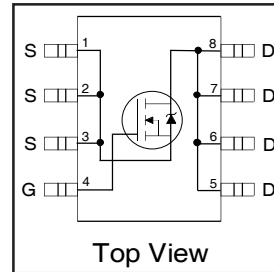


IRF7201PbF

- Generation V Technology
- Ultra Low On-Resistance
- N-Channel MOSFET
- Surface Mount
- Available in Tape & Reel
- Dynamic dv/dt Rating
- Fast Switching
- Lead-Free

HEXFET® Power MOSFET

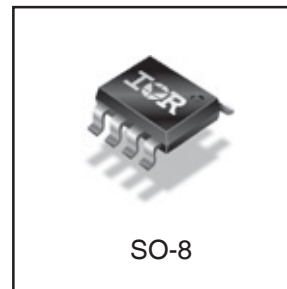


$V_{DS} = 30V$
$R_{DS(on)} = 0.030\Omega$

Description

Fifth Generation HEXFET® power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The SO-8 has been modified through a customized leadframe for enhanced thermal characteristics and multiple-die capability making it ideal in a variety of power applications. With these improvements, multiple devices can be used in an application with dramatically reduced board space. The package is designed for vapor phase, infra red, or wave soldering techniques. Power dissipation of greater than 0.8W is possible in a typical PCB mount application.



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain- Source Voltage	30	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	7.3	A
$I_D @ T_C = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	5.8	
I_{DM}	Pulsed Drain Current ①	58	
$P_D @ T_C = 25^\circ C$	Power Dissipation	2.5	W
$P_D @ T_C = 70^\circ C$	Power Dissipation	1.6	
	Linear Derating Factor	0.02	
V_{GS}	Gate-to-Source Voltage	± 20	V
V_{GSM}	Gate-to-Source Voltage Single Pulse $tp < 10\mu s$	30	V
E_{AS}	Single Pulse Avalanche Energy②	70	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.0	V/ns
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	$^\circ C$

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient⑤	—	50	$^\circ C/W$

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.024	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.030 0.050	Ω	$V_{GS} = 10V, I_D = 7.3A$ ④ $V_{GS} = 4.5V, I_D = 3.7A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	—	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
g_{fs}	Forward Transconductance	5.8	—	—	S	$V_{DS} = 15V, I_D = 2.3A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	1.0 25	μA	$V_{DS} = 24V, V_{GS} = 0V$ $V_{DS} = 24V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage Gate-to-Source Reverse Leakage	—	—	-100 100	nA	$V_{GS} = -20V$ $V_{GS} = 20V$
Q_g	Total Gate Charge	—	19	28	nC	$I_D = 4.6A$
Q_{gs}	Gate-to-Source Charge	—	2.3	3.5	nC	$V_{DS} = 24V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	6.3	9.5	nC	$V_{GS} = 10V$, See Fig. 10 ④
$t_{d(on)}$	Turn-On Delay Time	—	7.0	—	ns	$V_{DD} = 15V$
t_r	Rise Time	—	35	—	ns	$I_D = 4.6A$
$t_{d(off)}$	Turn-Off Delay Time	—	21	—	ns	$R_G = 6.2\Omega$
t_f	Fall Time	—	19	—	ns	$R_D = 3.2\Omega$, ④
C_{iss}	Input Capacitance	—	550	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	260	—	pF	$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	100	—	pF	$f = 1.0\text{MHz}$, See Fig. 9

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	2.5	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	58	A	
V_{SD}	Diode Forward Voltage	—	—	1.2	V	$T_J = 25^\circ\text{C}$, $I_S = 4.6A$, $V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	48	73	ns	$T_J = 25^\circ\text{C}$, $I_F = 4.6A$
Q_{rr}	Reverse Recovery Charge	—	73	110	nC	$di/dt = 100A/\mu s$ ⑤

Notes:

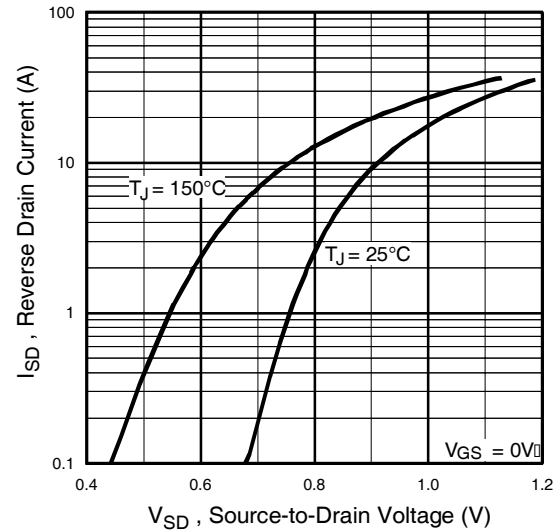
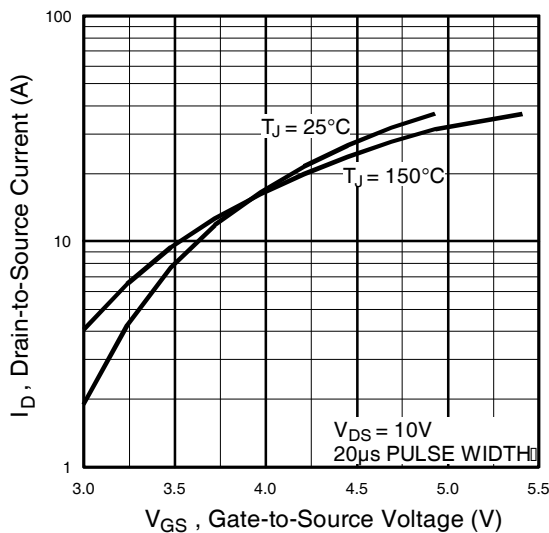
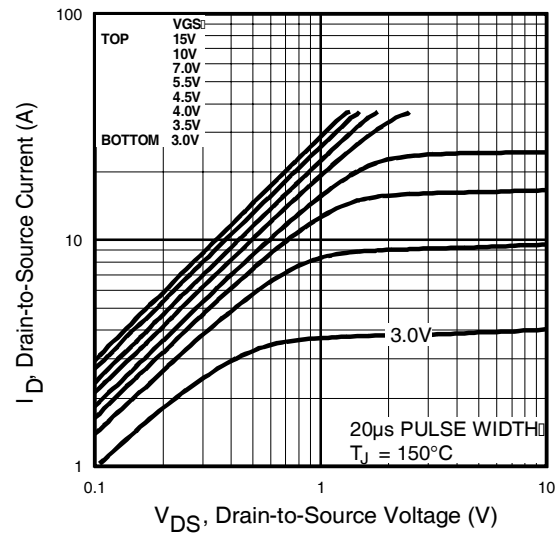
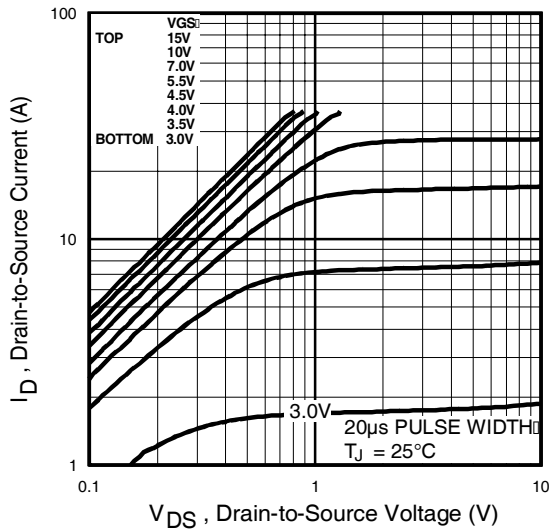
① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② $V_{DD} = 15V$, starting $T_J = 25^\circ\text{C}$, $L = 6.6\text{mH}$
 $R_G = 25\Omega$, $I_{AS} = 4.6A$. (See Figure 8)

③ $I_{SD} \leq 4.6A$, $di/dt \leq 120A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$,
 $T_J \leq 150^\circ\text{C}$

④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

⑤ When mounted on 1 inch square copper board, $t < 10\text{sec}$



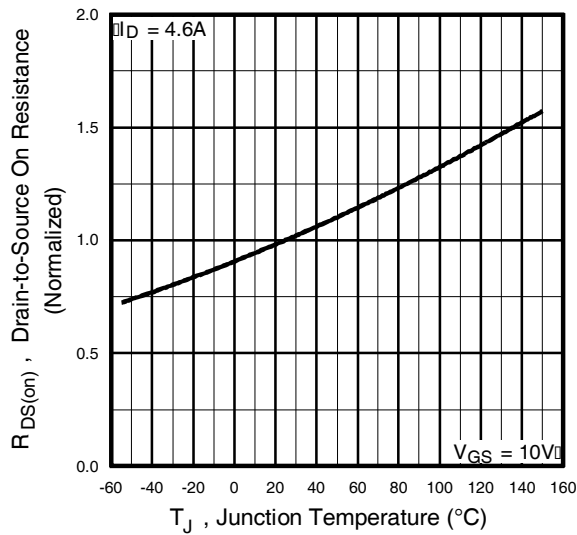


Fig 5. Normalized On-Resistance Vs. Temperature

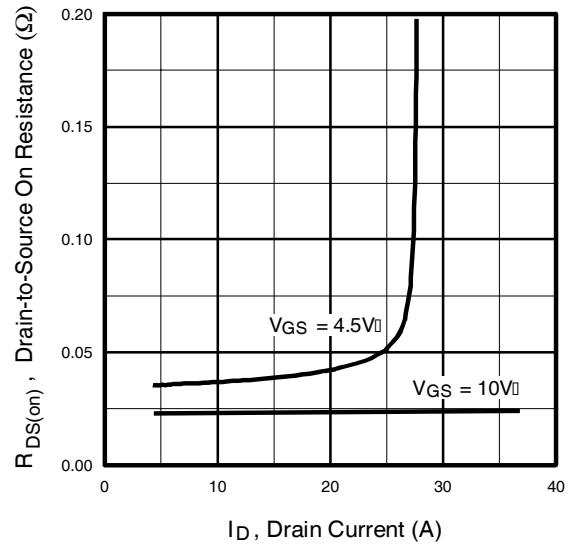


Fig 6. On-Resistance Vs. Drain Current

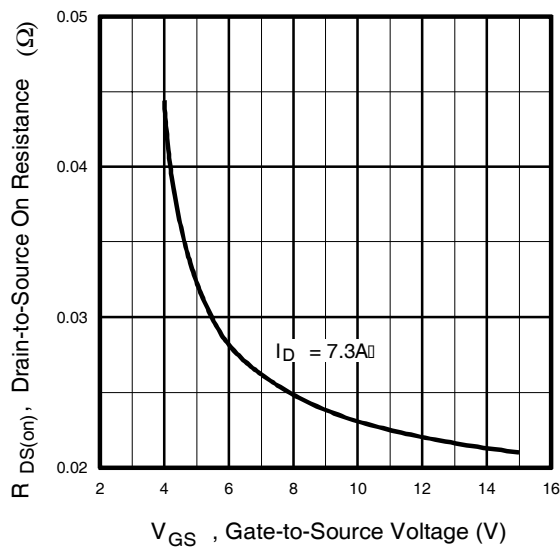


Fig 7. On-Resistance Vs. Gate Voltage

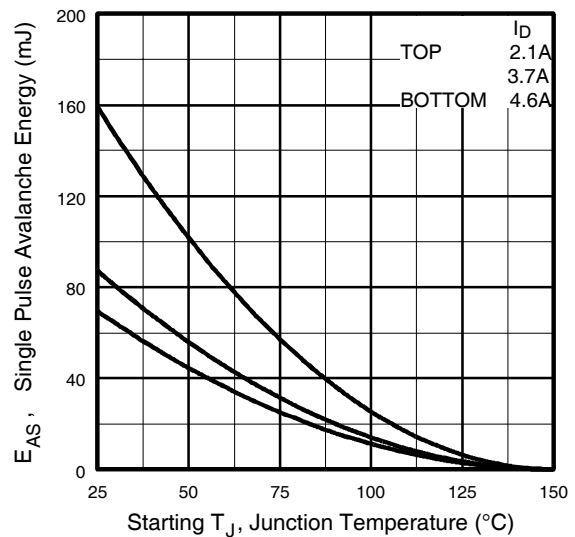


Fig 8. Maximum Avalanche Energy Vs. Drain Current

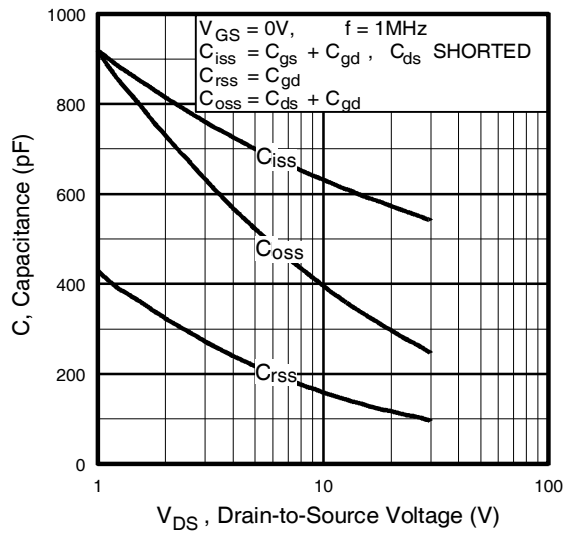


Fig 9. Typical Capacitance Vs. Drain-to-Source Voltage

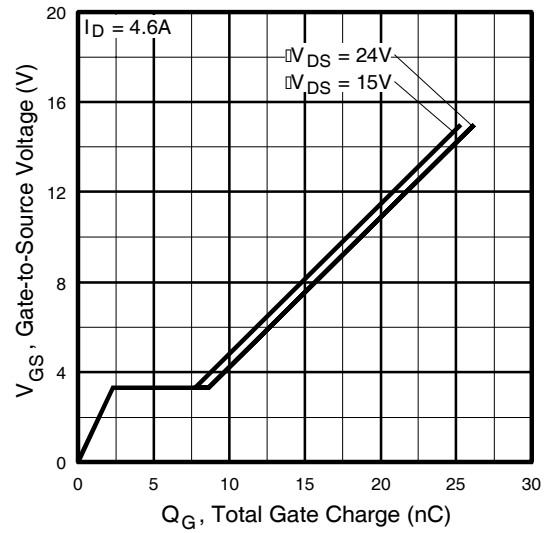


Fig 10. Typical Gate Charge Vs. Gate-to-Source Voltage

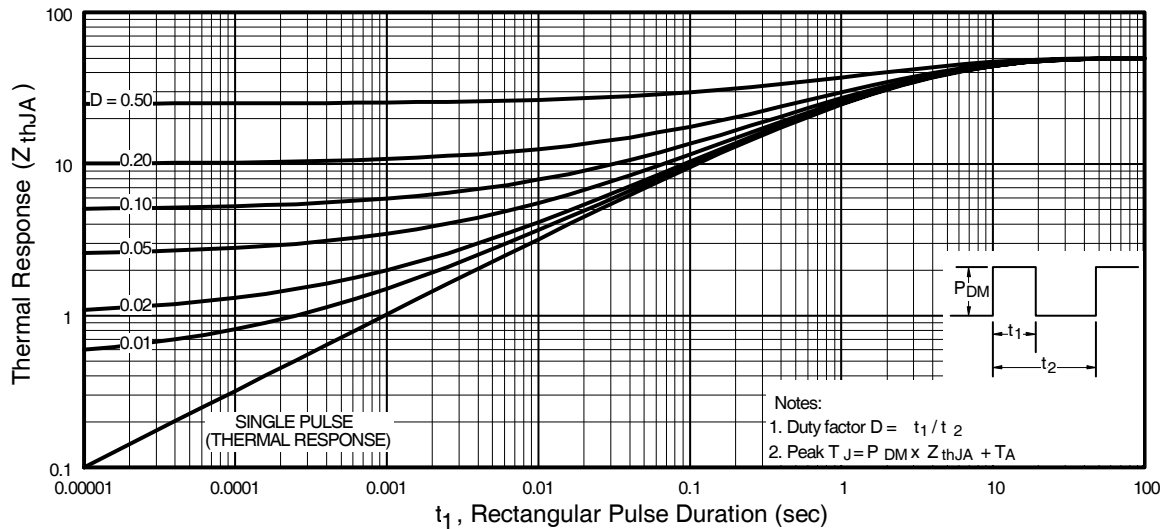


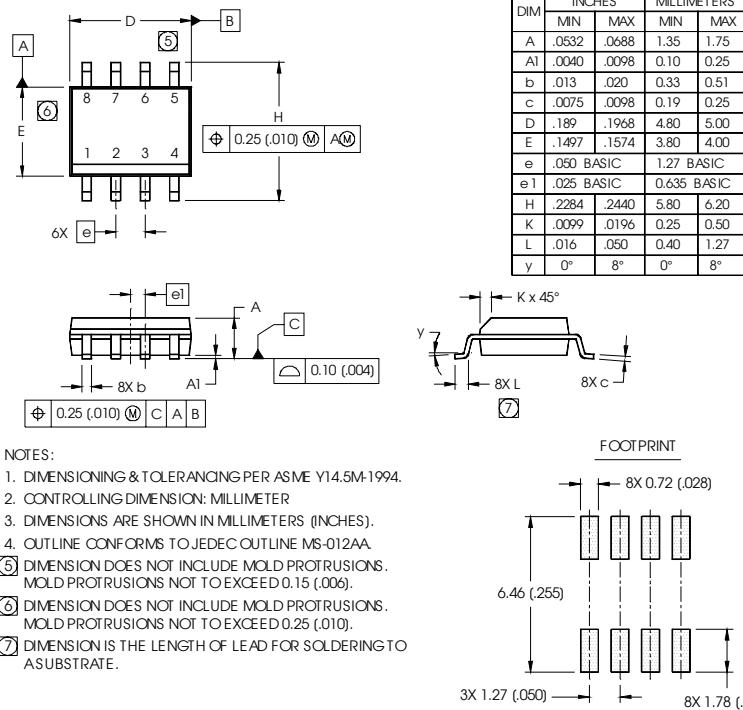
Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

IRF7201PbF

International
IR Rectifier

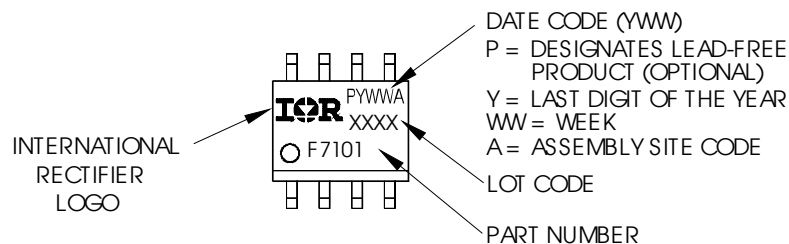
SO-8 Package Outline

Dimensions are shown in millimeters (inches)



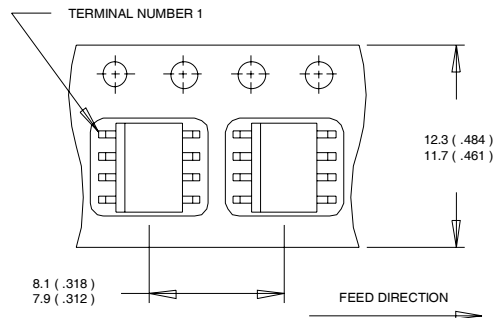
SO-8 Part Marking Information (Lead-Free)

EXAMPLE: THIS IS AN IRF7101 (MOSFET)

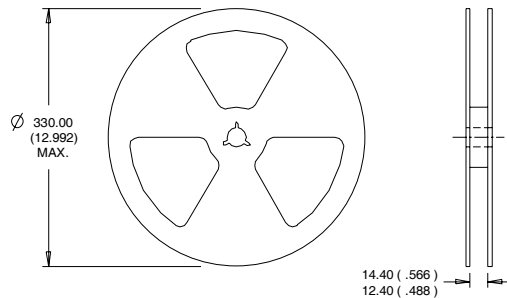


SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Data and specifications subject to change without notice.
This product has been designed and qualified for the Consumer market.
Qualifications Standards can be found on IR's Web site.

International
IR Rectifier

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